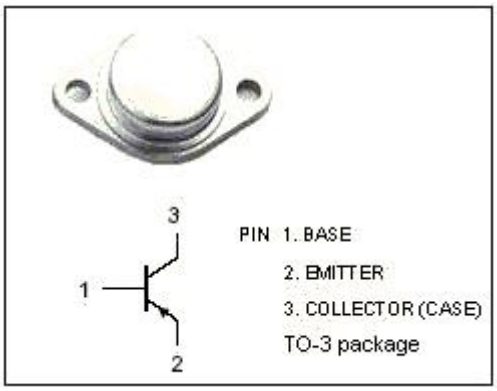
isc Silicon PNP Power Transistor 2N3197

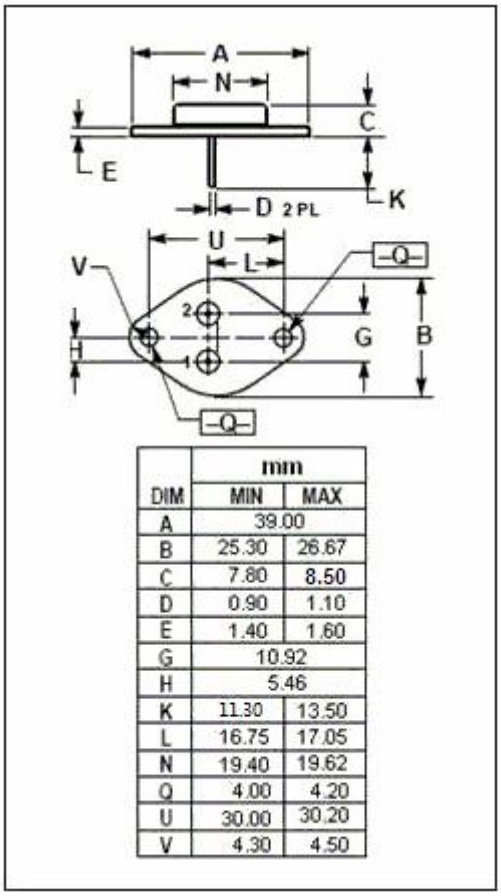
DESCRIPTION

- Excellent Safe Operating Area
- With TO-3 package
- Low collector saturation voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- For medium-speed switching and amplifier applications



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-10	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation@T_C=25℃	75	W
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-65~+200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.17	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.6A		-0.9	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; V_{CE}=-0.6V		-1.9	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -80V; I_B=0		-5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0		-1.0	mA
h_{FE}	DC Current Gain	I_C= -3A ; V_{CE}= -3V	10	30	